

METHOD OF INTEGRATING HIGH VOLT- AGE METAL OXIDE SEMICONDUCTOR DEVICES AND SUBMICRON METAL OXIDE SEMICONDUCTOR DEVICES

Abstract

The present invention provides a method of integrating at least one high voltage metal oxide semiconductor device and at least one Submicron metal oxide semiconductor device on a substrate. The method comprises: providing the substrate, forming a plurality of shallow trenches having different depths on a surface of the substrate, and forming a plurality of silicon oxide layers filling up the shallow trenches, and a top of each of the silicon oxide layers being in the shape of a mushroom.